

# NPN SILICON LOW NOISE RF TRANSISTOR

**DESCRIPTION:**

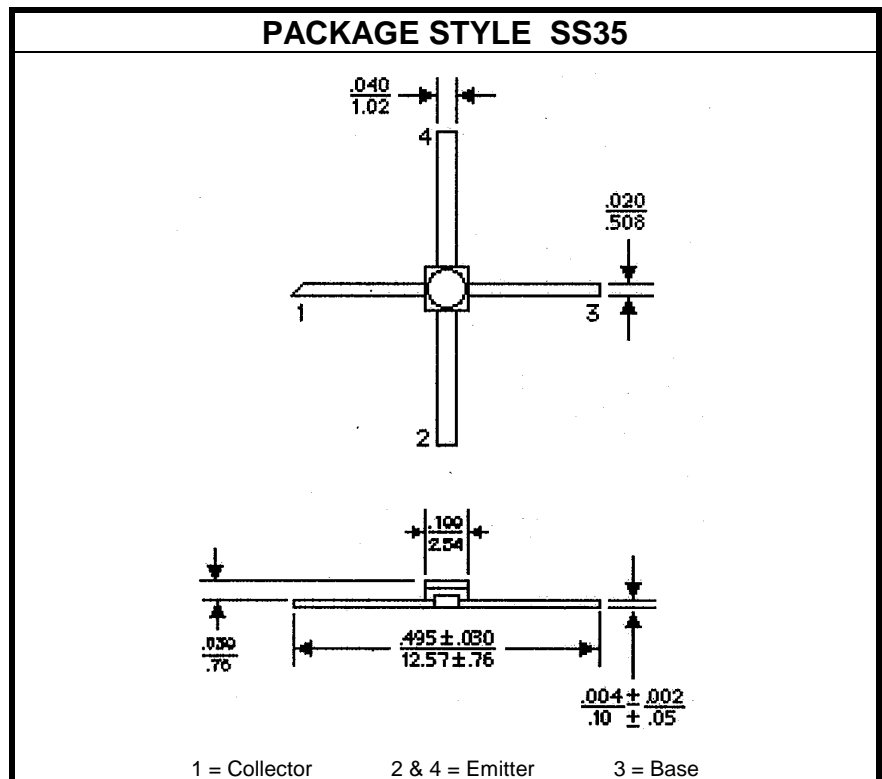
The **ASI 2N6603** is a Common Emitter Device Designed for Low Noise Class A Amplifier Applications.

**FEATURES INCLUDE:**

- $N_F = 2.9$  dB Typical @ 2 GHz
- $G_P = 11$  dB Typical @ 2 GHz
- Hermetic Metal Ceramic Package

**MAXIMUM RATINGS**

$I_C$	30 mA
$V_{CBO}$	25 V
$V_{CEO}$	15 V
$V_{EBO}$	3.0 V
$P_{DISS}$	400 mW @ $T_A = 125^\circ\text{C}$
$T_J$	$-65^\circ\text{C}$ to $+200^\circ\text{C}$
$T_{STG}$	$-65^\circ\text{C}$ to $+200^\circ\text{C}$


**CHARACTERISTICS**  $T_C = 25^\circ\text{C}$ 

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CEO}$	$I_C = 1.0$ mA			15			V
$BV_{CBO}$	$I_C = 100$ nA			25			V
$BV_{EBO}$	$I_E = 100$ nA			3.0			V
$I_{CBO}$	$V_{CB} = 15$ V					50	nA
$h_{FE}$	$V_{CE} = 10$ V	$I_C = 15$ mA		30		200	---
$C_{CB}$	$V_{CB} = 10$ V	$f = 1.0$ MHz		0.25		0.75	pF
$P_G$ $NF$	$V_{CE} = 10$ V	$I_C = 15$ mA	$f = 2.0$ GHz		11 2.9		dB